

SKM200GB102D

Half Bridge IGBT Power Module - With inverse diodes.

Semikron

Circuits Per Package=1

$V_{(BR)CES} (V)=1.0k$

$V_{(BR)GES} (V)=20$

$I_{(C) Abs. (A) Collector Current}=200$

Absolute Max. Power Diss. (W)=1.25k

$I_{(CES) Min. (A)}=2.0m$

$I_{(GES) Max. (A)}=100n$

$V_{(CE)sat Max. (V)}=4.8$

$t_{(r) Max. (s) Rise time}=450n$

$t_{(d)off Max. (s) Off time}=1.1\mu$

$t_{(f) Max. (s) Fall time.}=450n$

Package=MODULE-var